# **BUK7K25-40E**

# **Dual N-channel TrenchMOS standard level FET**

23 April 2013

**Product data sheet** 

# 1. General description

Dual standard level N-channel MOSFET in a LFPAK56D package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V<sub>GS(th)</sub> > 1 V @ 175 °C

# 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- · Start-stop micro-hybrid applications
- · Transmission control
- Ultra high performance power switching

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; Tmb = 25 °C; <u>Fig. 1</u>		-	-	27	Α	
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	32	W	
Static characte	Static characteristics FET1 and FET2							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 12$		-	21.25	25	mΩ	
Dynamic chara	Dynamic characteristics FET1 and FET2							
$Q_{GD}$	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 20 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 14; Fig. 15$		-	2.6	-	nC	



#### **Dual N-channel TrenchMOS standard level FET**

# **Pinning information**

Table 2. **Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1	1/	
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2	O O O O	mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1	2.17.11335 (3311233)	

# **Ordering information**

Table 3. **Ordering information** 

Type number	Package					
	Name	Description	Version			
BUK7K25-40E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

#### **Marking** 7.

Table 4. Marking codes

Type number	Marking code
BUK7K25-40E	72540E

#### **Limiting values** 8.

Table 5. **Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	IV	/lin	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-		40	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 kΩ; $T_j \ge 25$ °C; $T_j \le 175$ °C	-		40	V
$V_{GS}$	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC	-:	20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; Tmb = 25 °C; <u>Fig. 1</u>	-		27	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	-		19	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 4	-		107	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-		32	W
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Symbol	Parameter	Conditions		Min	Max	Unit	
T <sub>stg</sub>	storage temperature			-55	175	°C	
T <sub>j</sub>	junction temperature			-55	175	°C	
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C	
Source-drain diode FET1 and FET2							
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	27	Α	
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	107	Α	
Avalanche Ruggedness FET1 and FET2							
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 28 \text{ A}; V_{sup} \le 40 \text{ V}; V_{GS} = 10 \text{ V};$ $T_{j(init)} = 25 \text{ °C}; Fig. 3$	[1][2]	-	10	mJ	

- [1] Refer to application note AN10273 for further information
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

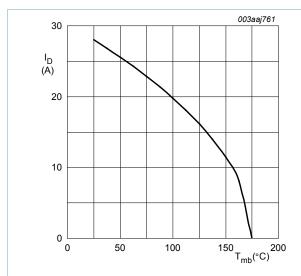


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 10 V$$

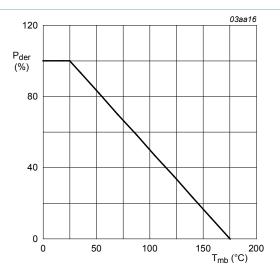


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \,\%$$

#### **Dual N-channel TrenchMOS standard level FET**

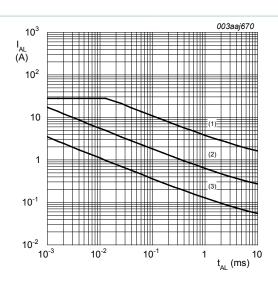


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

- (1) Single-pulse;  $T_j = 25 \,^{\circ}C$ .
- (2) Single-pulse; T<sub>j</sub> = 150 °C.(3) Repetitive.

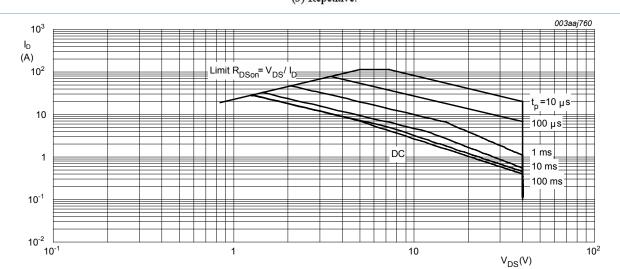


Fig. 4. Safe operating area; continuous and peak drain current as a function of drain-source voltage

 $T_{mb} = 25 \,^{\circ}C$ ;  $I_{DM}$  is single pulse

### 9. Thermal characteristics

Table 6. Thermal characteristics

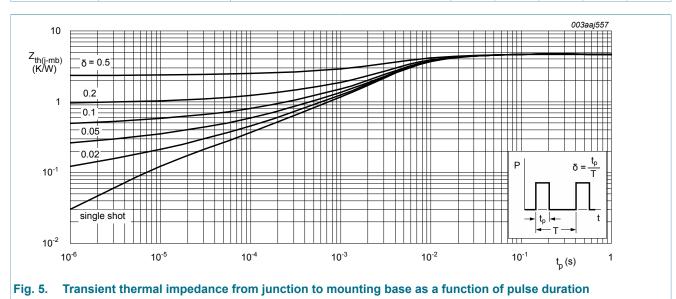
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	4.68	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W



### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics FET1 and FET2		'			
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10; Fig. 11	2.4	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 10; Fig. 11	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10; Fig. 11	-	-	4.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; Fig. 12	-	21.25	25	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 13	-	40.1	49.3	mΩ

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#### **Dual N-channel TrenchMOS standard level FET**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	naracteristics FET1 and FE	T2	1			
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V;	-	7.9	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 14; Fig. 15</u>	-	1.5	-	nC
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 20 V; T <sub>j</sub> = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	2.6	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	394	525	pF
C <sub>oss</sub>	output capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	107	128	pF
C <sub>rss</sub>	reverse transfer capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	76	104	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 32 V; $R_{L}$ = 6.5 $\Omega$ ; $V_{GS}$ = 10 V;	-	4.4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C; I_D = 5 A$	-	4.5	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	8.3	-	ns
t <sub>f</sub>	fall time		-	5.2	-	ns
Source-dra	in diode FET1 and FET2	1	1			
$V_{SD}$	source-drain voltage	$I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$	-	0.78	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	12.4	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C	-	6.7	-	nC

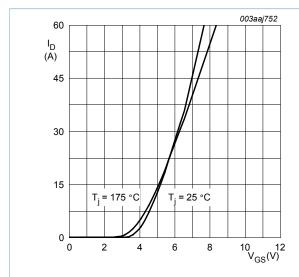


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

 $V_{DS} = 10V$ 

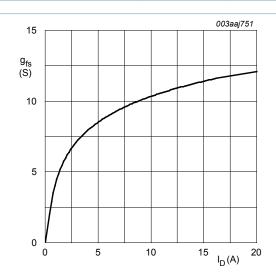


Fig. 7. Forward transconductance as a function of drain current; typical values

$$T_j = 25\,{}^{\circ}C; V_{DS} = 15\,V$$

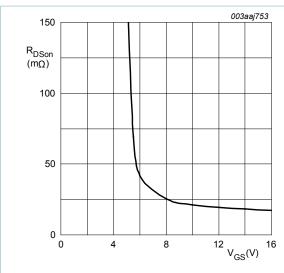


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25 \,^{\circ}C; \ I_D = 5A$$

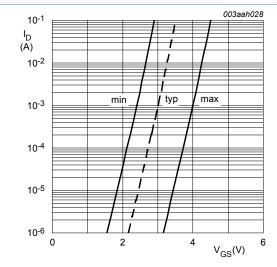


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C;  $V_{DS} = 5V$ 

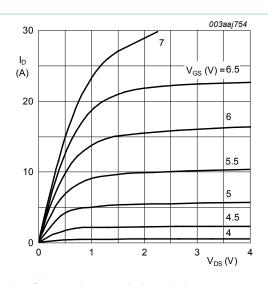


Fig. 9. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25 \,^{\circ}C$$

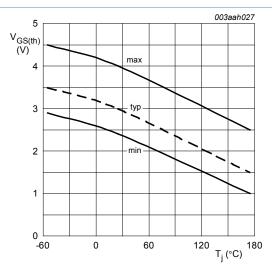


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

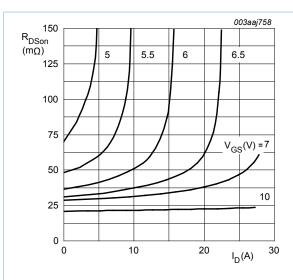


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C$$

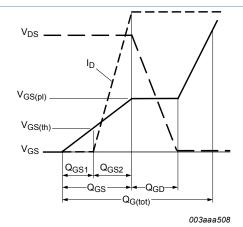


Fig. 14. Gate charge waveform definitions

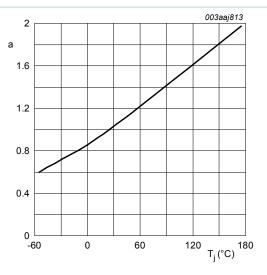


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

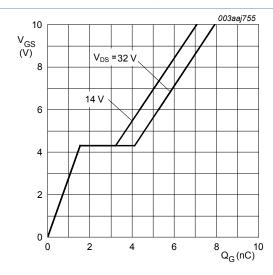


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25 \,^{\circ}C; I_D = 5A$$

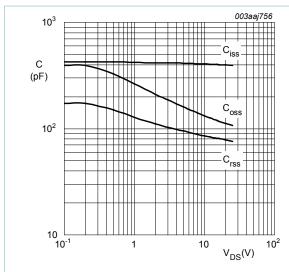
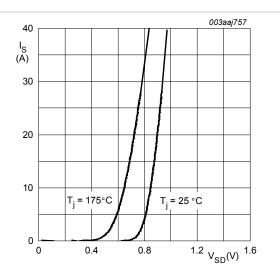


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Source current as a function of source-drain as a function of drain-source voltage; typical values

$$V_{GS} = 0 V; f = 1MHz$$



voltage; typical values

$$V_{GS} = 0 V$$

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# 11. Package outline

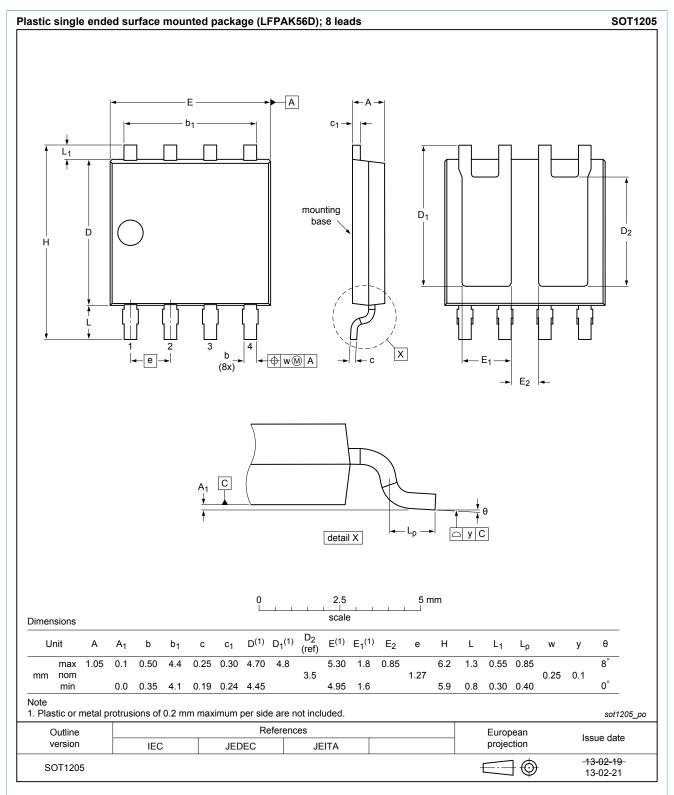


Fig. 18. Package outline LFPAK56D (SOT1205)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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